

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-5. (Canceled)

6. (Original) A method of manufacturing a light emitting device, said method comprising:
forming at least a transparent protrusion;
forming a pixel electrode to overlap the transparent protrusion;
forming an organic layer to overlap the pixel electrode; and
forming a cathode over the organic layer.

7. (Currently amended) A personal computer comprising a main body, a casing, a display portion, a keyboard, said personal computer including a light emitting device:
wherein said light emitting device comprises:
at least a transparent protrusion;
a pixel electrode over the transparent protrusion;
an organic layer over the pixel electrode; and
a cathode over the organic layer,
wherein a surface of the cathode in contact with the organic layer is uneven.

8. (Original) A personal computer according to claim 7, further comprising:
an insulating film in transverse direction of the transparent protrusion,
wherein the insulating film has a high light absorption property.

9. (Original) A personal computer according to claim 7,

wherein the transparent protrusion is a microlens.

10. (Original) A portable telephone comprising a main body, a sound output portion, a sound input portion, a display portion, operation switches, and an antenna, said portable telephone including a light emitting device:

wherein said light emitting device comprises:

- at least a transparent protrusion;
- a pixel electrode over the transparent protrusion;
- an organic layer over the pixel electrode; and
- a cathode over the organic layer,

wherein a surface of the cathode in contact with the organic layer is uneven.

11. (Original) A portable telephone according to claim 10, further comprising:
an insulating film in a transverse direction of the transparent protrusion,
wherein the insulating film has a high light absorption property.

12. (Original) A portable telephone according to claim 10,
wherein the transparent protrusion is a microlens.

13. (Original) A portable telephone according to claim 10, further comprising an
operation panel, a connecting portion, and a power source switch.

14. (New) A method according to claim 6, further comprising:
forming an insulating film in a transverse direction of the transparent protrusion, wherein
the insulating film has a high light absorption property.

15. (New) A method according to claim 6, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor;

forming a first opening in the insulating film;

forming a wire over the insulating film, wherein the wire is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

16. (New) A method according to claim 6, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;

forming a first opening in the insulating film;

forming a wire over the insulating film, wherein the wire is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

17. (New) A method according to claim 6, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wire over the first insulating film, wherein the wire is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film; and

forming a second opening in the second insulating film.

18. (New) A method according to claim 6, further comprising:
- forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
 - forming a first insulating film over the thin film transistor;
 - forming a first opening in the first insulating film;
 - forming a wire over the first insulating film, wherein the wire is electrically connected to the semiconductor film through the first opening;
 - forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a high light absorption property; and
 - forming a second opening in the second insulating film.
19. (New) A method according to claim 6, wherein the transparent protrusion includes a microlens.